Supporting Information for:

Graphene CVD: Interplay Between Growth and Etching on Morphology and Stacking by Hydrogen and Oxidizing Impurities

Saman Choubak[¶], Pierre L. Levesque[¥], Etienne Gaufres[¥], Maxime Biron[¶], Patrick Desjardins[¶]*, and Richard Martel [¥]*

¶ Regroupement Québécois sur les Matériaux de Pointe (RQMP) and Département de Génie Physique, Polytechnique Montréal, Montréal, C.P. 6079, Succursale Centre-ville, Montréal, Québec H3C 3A7, Canada

¥ Regroupement Québécois sur les Matériaux de Pointe (RQMP) and Département de Chimie, Université de Montréal, C.P. 6128, Succursale Centre-Ville, Montréal, Québec H3C 3J7, Canada

1. Graphene sample annealed in unpurified hydrogen at 950 °C transferred on SiO_2/Si

Figure S1 is the SEM image of the transferred graphene sample presented in Fig 1b. It also shows the Raman spectra for this sample. Based on the SEM image contrast and Raman measurement, it is confirmed that the small patches are indeed the remaining graphene.

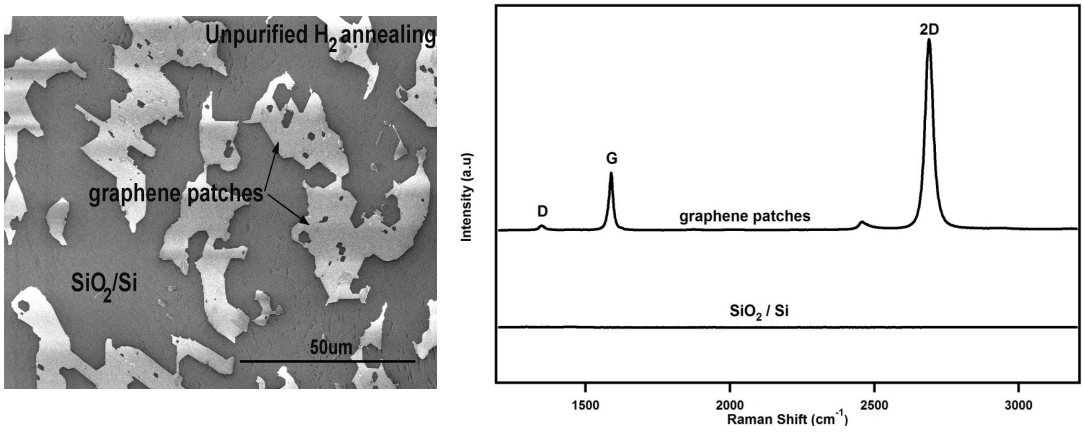

Figure S1. SEM image and Raman spectra of the unpurified hydrogen annealed sample as shown in Fig. 1b at 950 °C for 30 min transferred on SiO_2/Si.